## EE143 Lab Week 8 Measurement Checklist: Created: 2006/02/20, Shong Yin

| 1) | Lithography |
|----|-------------|
| 1) | Limography  |

| Time (sec)       |  |
|------------------|--|
| Softbake:        |  |
| <b>Exposure:</b> |  |
| Developer:       |  |
| Hardbake:        |  |

| Linewidth (um) of Photoresist |          |            |
|-------------------------------|----------|------------|
| Nominal                       | Measured | % Overetch |
| 2                             |          |            |
| 3                             |          |            |
| 4                             |          |            |
| 8                             |          |            |

Notes: 1 tick mark in the right eyepiece of microscope is 1um under 100X

## Take a photo of the linewidth marks under 50X

| Vernier Misalignment: |  |
|-----------------------|--|
| X                     |  |
| Y                     |  |

Take 3 Photos: Overall Vernier Pattern under 20X, and zoomed photo of X & Y vernier patterns under 50X

## 2) Contact Cut

| Contact Etch Time: |  |
|--------------------|--|

| Linewidth (um) of Contact after etch |          |            |
|--------------------------------------|----------|------------|
| Nominal                              | Measured | % Overetch |
| 2                                    |          |            |
| 3                                    |          |            |
| 4                                    |          |            |
| 8                                    |          |            |

Notes: 1 tick mark in the right eyepiece of microscope is 1um under 100X

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Calculate % overetch of the linewidth patterns

What was a visual method for determining completion of etching?